

PMN22XN

30 V, single N-channel Trench MOSFET Rev. 1 — 19 January 2012

Product data sheet

Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching

■ Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	[1]	-	-	5.7	Α
Static charac	teristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5.7 \text{ A}; T_j = 25 \text{ °C}$		-	21	27	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	D. D. D.	D.
2	D	drain	<u> </u>	
3	G	gate		
4	S	source	1 1 2 3	
5	D	drain	SOT457 (TSOP6)	\$ 017aaa253
6	D	drain		017aaa233



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3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMN22XN	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457	

4. Marking

Table 4. Marking codes

Type number	Marking code
PMN22XN	A4

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	5.7	Α
		$V_{GS} = 4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	3.6	Α
I_{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \text{ µs}$		-	23	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	545	mW
			[1]	-	1390	mW
		T _{sp} = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	1.5	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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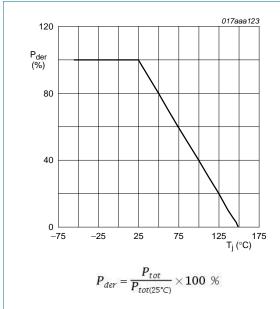


Fig 1. Normalized total power dissipation as a function of junction temperature

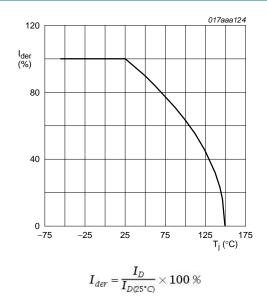
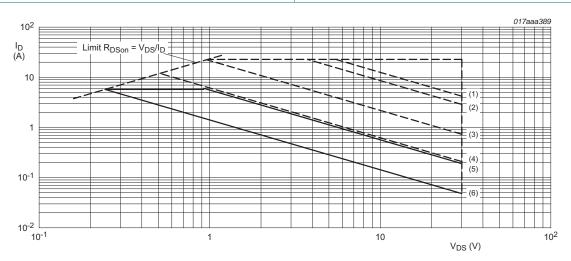


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

(1) $t_p = 100 \mu s$

(2) $t_p = 1 \text{ ms}$

(3) $t_p = 10 \text{ ms}$

(4) $t_p = 100 \text{ ms}$

(5) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$

(6) DC; T_{amb} = 25 °C; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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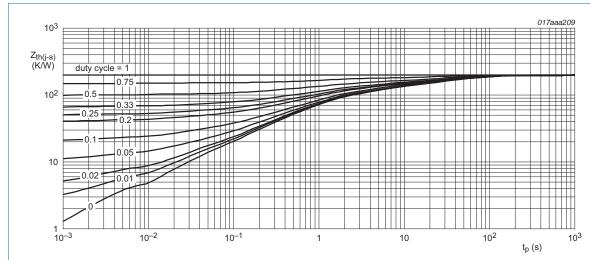
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Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u>	-	200	230	K/W
			[2]	-	78	90	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

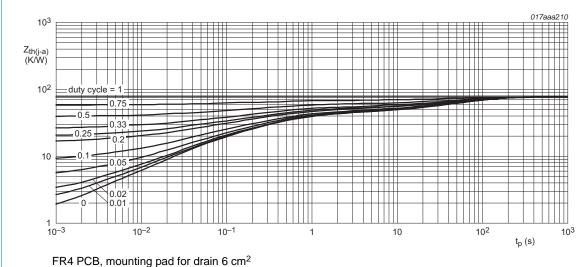


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.5	1	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	20	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 5.7 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	21	27	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5.7 \text{ A}; T_j = 150 \text{ °C}$	-	34	43	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	28	37	mΩ
9fs	forward transconductance	$V_{DS} = 5 \text{ V}; I_{D} = 3 \text{ A}; T_{j} = 25 ^{\circ}\text{C}$	-	17	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 3 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	6.4	10	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.6	-	nC
Q_{GD}	gate-drain charge		-	1.1	-	nC
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	585	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	1.8	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; I_D = 4.8 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	12	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	27	-	ns
t _{d(off)}	turn-off delay time		-	128	-	ns
t _f	fall time		-	68	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 1.5 A; V _{GS} = 0 V; T _i = 25 °C	-	0.75	1.2	V

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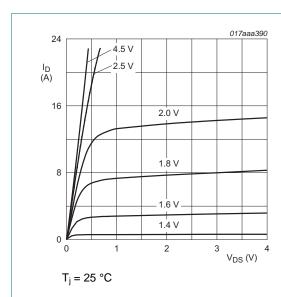
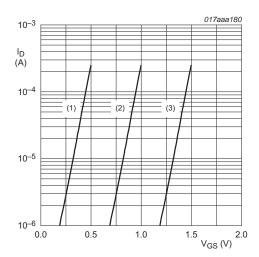


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



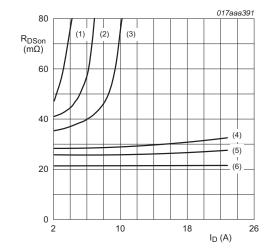
 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_i = 25 \, ^{\circ}C$

(1) $V_{GS} = 1.7 V$

(2) $V_{GS} = 1.8 \text{ V}$

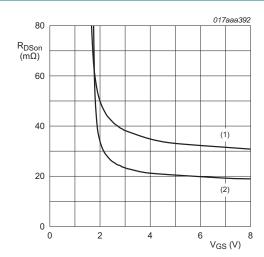
(3) $V_{GS} = 1.9 \text{ V}$

(4) $V_{GS} = 2.5 \text{ V}$

(5) $V_{GS} = 3.0 \text{ V}$

(6) $V_{GS} = 4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 5.7 A$

(1) $T_i = 150 \,^{\circ}\text{C}$

(2) $T_j = 25$ °C

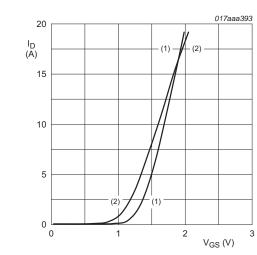
Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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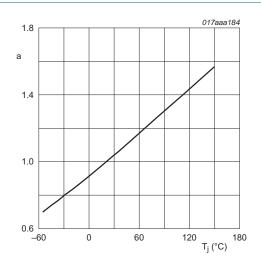


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_i = 25 \, ^{\circ}C$$

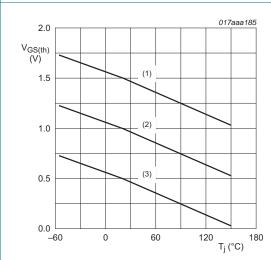
(2) $T_j = 150 \, ^{\circ}\text{C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

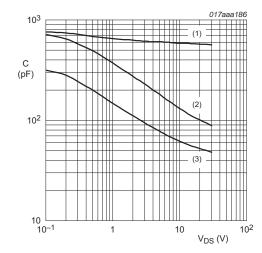
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



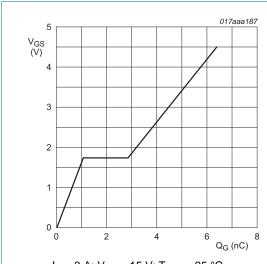
 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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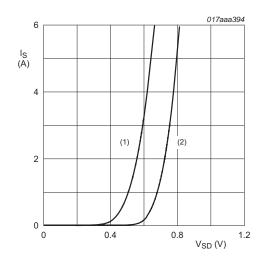
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 $I_D = 3 \text{ A}; V_{DS} = 15 \text{ V}; T_{amb} = 25 \text{ °C}$

Fig 15. Gate charge waveform definitions





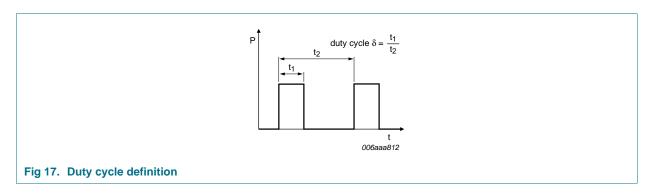
 $V_{GS} = 0 \text{ V}$ (1) $T_j = 150 \text{ }^{\circ}\text{C}$

(2) $T_j = 25 \,{}^{\circ}\text{C}$

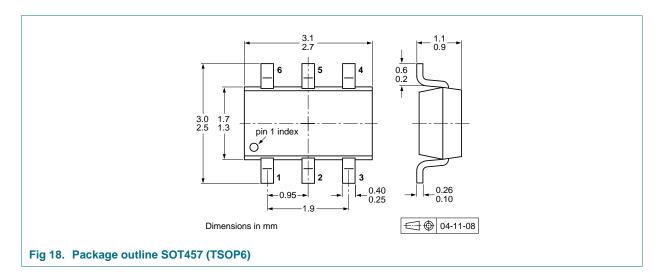
Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



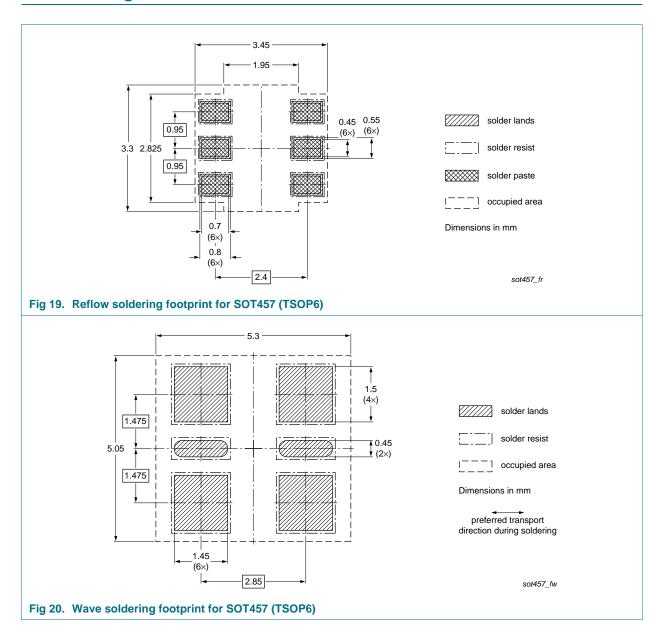
9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMN22XN v.1	20120119	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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